Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability: Ptot = 980 mW
- ElectroStatic Discharge (ESD) protection 2 kV HBM
- AEC-Q101 qualified

3. Applications

- LED driver
- Power management
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-5.6	Α
Static characte	eristics						,
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -4.5 A; T_j = 25 °C		-	27	32	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



20 V, P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV27UPEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV27UPEA	AE%

[1] % = placeholder for manufacturing site code

20 V, P-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-5.6	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-4.5	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-2.8	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-18	Α
E _{DS(AL)R}	repetitive drain-source avalanche energy	I_D = -1.8 A; $T_{j(init)}$ = 25 °C; DUT in avalanche (unclamped).		-	19	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	490	mW
			[1]	-	980	mW
		T _{sp} = 25 °C		-	4150	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.2	Α
ESD maximu	m rating		•			
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Measured between all pins.

20 V, P-channel Trench MOSFET

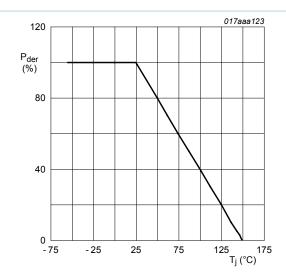


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

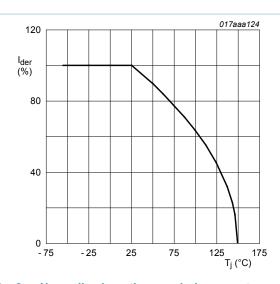
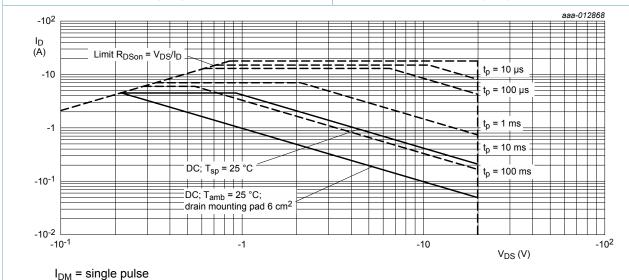


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



DW - 3 - 1- - -

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance		[1]	-	222	255	K/W
	from junction to ambient		<u>[2]</u>	-	111	128	K/W
		in free air; t ≤ 5 s	<u>[2]</u>	-	74	85	K/W

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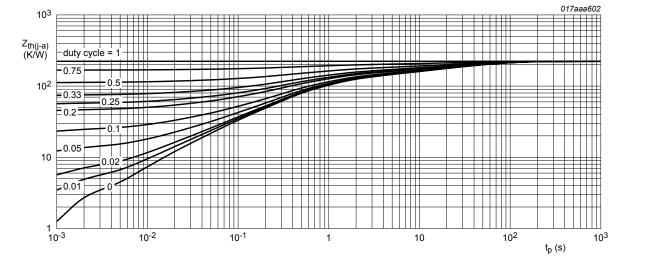
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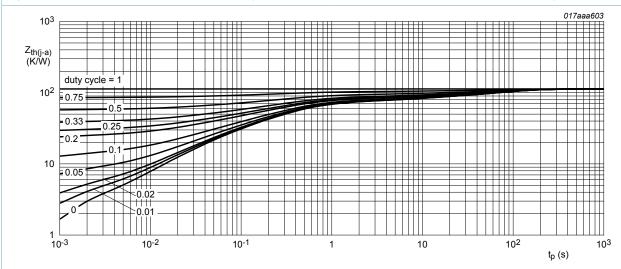
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	25	30	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, P-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Table 7.	Characteristics	Conditions	B#!	Ture	Mess	11mi4
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	##A
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-5	μA
R _{DSon} drain-source on-state resistance		$V_{GS} = -4.5 \text{ V}; I_D = -4.5 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	27	32	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -4.5 A; T _j = 150 °C	-	40	48	mΩ
		V_{GS} = -2.5 V; I_D = -3.8 A; T_j = 25 °C	-	38	45	mΩ
	V_{GS} = -1.8 V; I_D = -3 A; T_j = 25 °C	-	50	63	mΩ	
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_{D} = -2 A; T_{j} = 25 °C	-	15	-	S
R _G	gate resistance	f = 1 MHz	-	10.7	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -4.4 A; V_{GS} = -4.5 V;	-	14.7	22.1	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	2.6	-	nC
Q_{GD}	gate-drain charge		-	2.5	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	1820	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	208	-	pF
C _{rss}	reverse transfer capacitance		-	146	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -4.4 A; V_{GS} = -4.5 V;	-	11	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 ^{\circ}C$	-	30	-	ns
t _{d(off)}	turn-off delay time		-	83	-	ns
t _f	fall time		-	39	-	ns
Source-d	rain diode		I	1	1	1
V_{SD}	source-drain voltage	I _S = -1.2 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.7	-1.2	V

20 V, P-channel Trench MOSFET

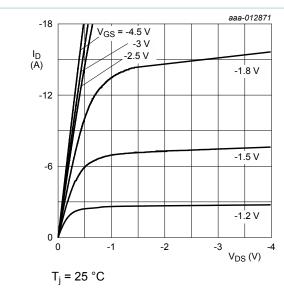


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

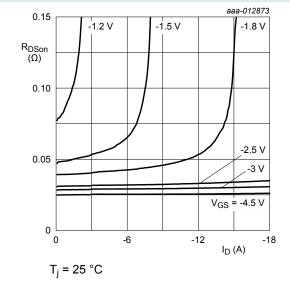


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

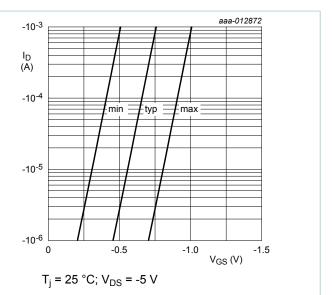


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

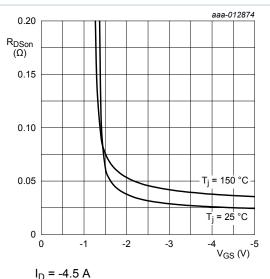


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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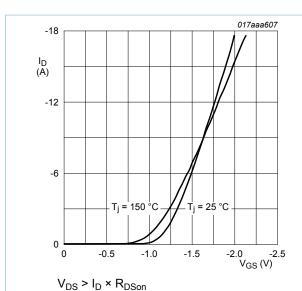


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

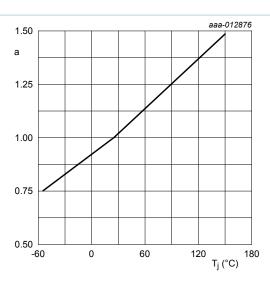


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

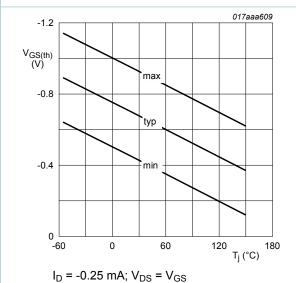
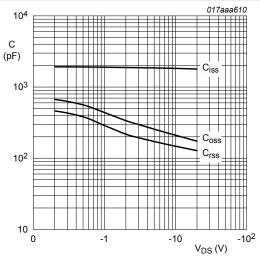


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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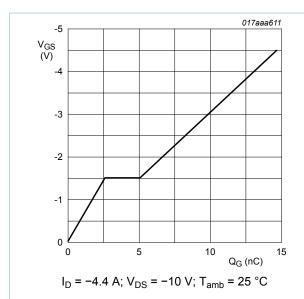


Fig. 14. Gate-source voltage as a function of gate charge; typical values

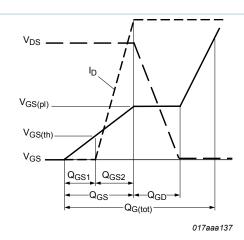


Fig. 15. MOSFET transistor: Gate charge waveform definitions

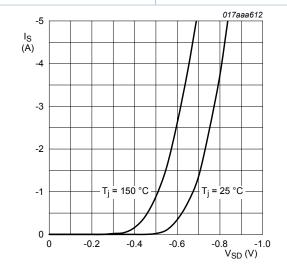
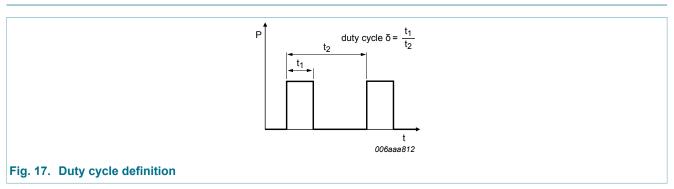


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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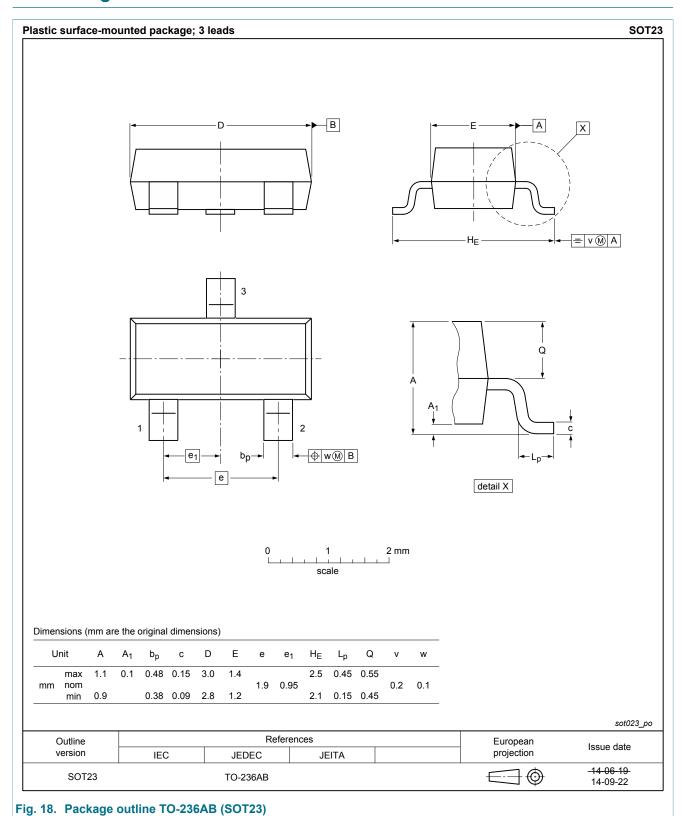
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11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

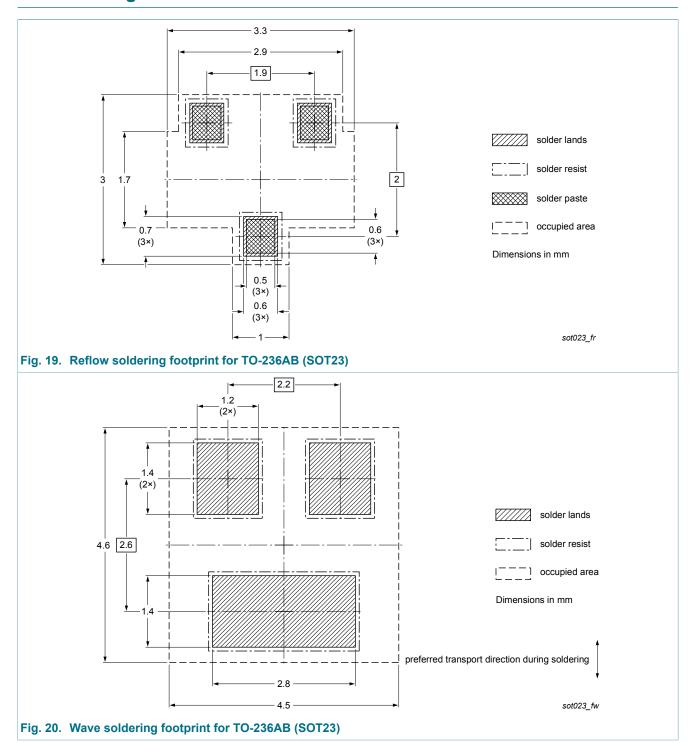
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV27UPEA v.1	20151030	Product data sheet	-	-

20 V, P-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	9
11.1	Quality information	10
12	Package outline	11
13	Soldering	12
14	Revision history	13
15	Legal information	14
15.1	Data sheet status	14
15.2	Definitions	14
15.3	Disclaimers	14
15.4	Trademarks	15

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